



SANYO Semiconductors

# DATA SHEET

An ON Semiconductor Company

N-Channel Silicon MOSFET

## ATP201 — General-Purpose Switching Device Applications

### Features

- Low ON-resistance.
- 4.5V drive.
- Slim package.
- Halogen free compliance.

### Specifications

Absolute Maximum Ratings at Ta=25°C

Parameter	Symbol	Conditions	Ratings	Unit
Drain-to-Source Voltage	V <sub>DSS</sub>		30	V
Gate-to-Source Voltage	V <sub>GSS</sub>		±20	V
Drain Current (DC)	I <sub>D</sub>		35	A
Drain Current (PW≤10μs)	I <sub>DP</sub>	PW≤10μs, duty cycle≤1%	105	A
Allowable Power Dissipation	P <sub>D</sub>	T <sub>c</sub> =25°C	30	W
Channel Temperature	T <sub>ch</sub>		150	°C
Storage Temperature	T <sub>stg</sub>		-55 to +150	°C
Avalanche Energy (Single Pulse) *1	E <sub>AS</sub>		10	mJ
Avalanche Current *2	I <sub>AV</sub>		18	A

Note : \*1 V<sub>DD</sub>=10V, L=50μH, I<sub>AV</sub>=18A

\*2 L≤50μH, Single pulse

Electrical Characteristics at Ta=25°C

Parameter	Symbol	Conditions	Ratings			Unit
			min	typ	max	
Drain-to-Source Breakdown Voltage	V <sub>(BR)DSS</sub>	I <sub>D</sub> =1mA, V <sub>GS</sub> =0V	30			V
Zero-Gate Voltage Drain Current	I <sub>DSS</sub>	V <sub>DS</sub> =30V, V <sub>GS</sub> =0V			1	μA
Gate-to-Source Leakage Current	I <sub>GSS</sub>	V <sub>GS</sub> =±16V, V <sub>DS</sub> =0V			±10	μA

Marking : ATP201

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# ATP201

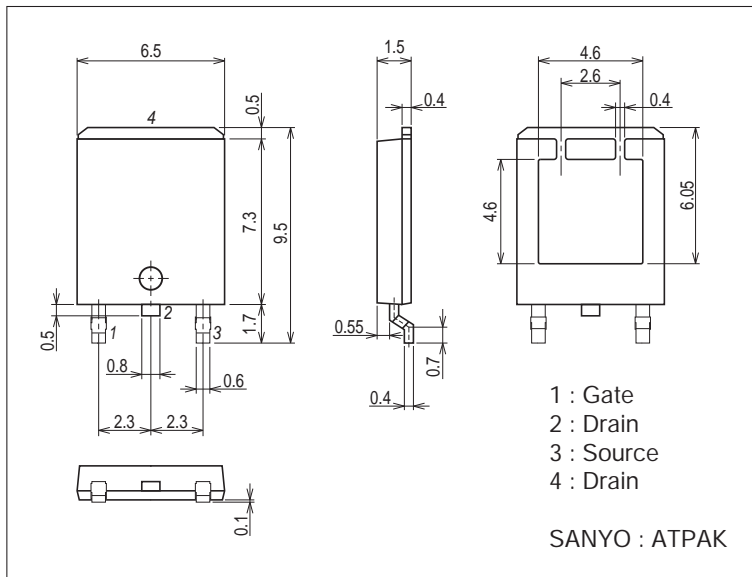
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Parameter	Symbol	Conditions	Ratings			Unit
			min	typ	max	
Cutoff Voltage	$V_{GS(off)}$	$V_{DS}=10V, I_D=1mA$	1.2		2.6	V
Forward Transfer Admittance	$ y_{fs} $	$V_{DS}=10V, I_D=18A$		24		S
Static Drain-to-Source On-State Resistance	$R_{DS(on)1}$	$I_D=18A, V_{GS}=10V$		13	17	$m\Omega$
	$R_{DS(on)2}$	$I_D=9A, V_{GS}=4.5V$		23	33	$m\Omega$
Input Capacitance	$C_{iss}$	$V_{DS}=10V, f=1MHz$		985		pF
Output Capacitance	$C_{oss}$	$V_{DS}=10V, f=1MHz$		180		pF
Reverse Transfer Capacitance	$C_{rss}$	$V_{DS}=10V, f=1MHz$		100		pF
Turn-ON Delay Time	$t_{d(on)}$	See specified Test Circuit.		10		ns
Rise Time	$t_r$	See specified Test Circuit.		230		ns
Turn-OFF Delay Time	$t_{d(off)}$	See specified Test Circuit.		51		ns
Fall Time	$t_f$	See specified Test Circuit.		39		ns
Total Gate Charge	$Q_g$	$V_{DS}=15V, V_{GS}=10V, I_D=35A$		17		nC
Gate-to-Source Charge	$Q_{gs}$	$V_{DS}=15V, V_{GS}=10V, I_D=35A$		4.7		nC
Gate-to-Drain "Miller" Charge	$Q_{gd}$	$V_{DS}=15V, V_{GS}=10V, I_D=35A$		2.8		nC
Diode Forward Voltage	$V_{SD}$	$I_S=35A, V_{GS}=0V$		0.97	1.2	V

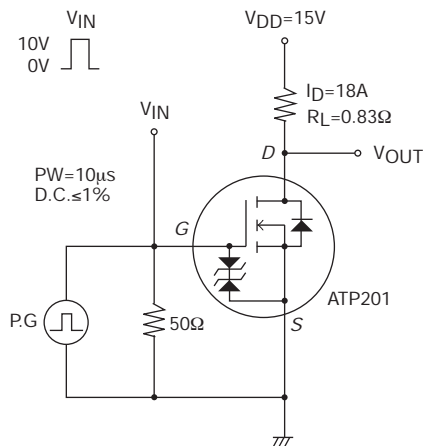
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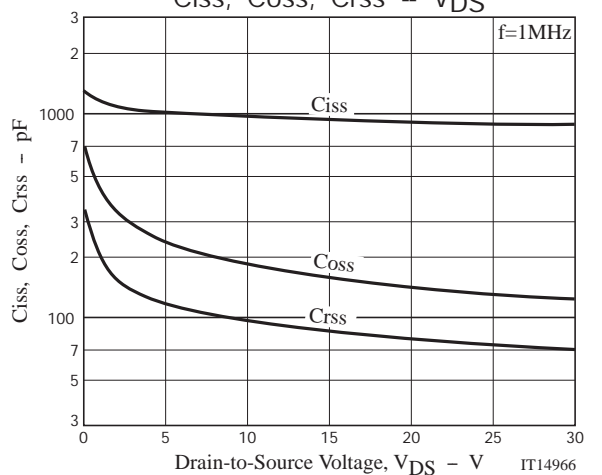
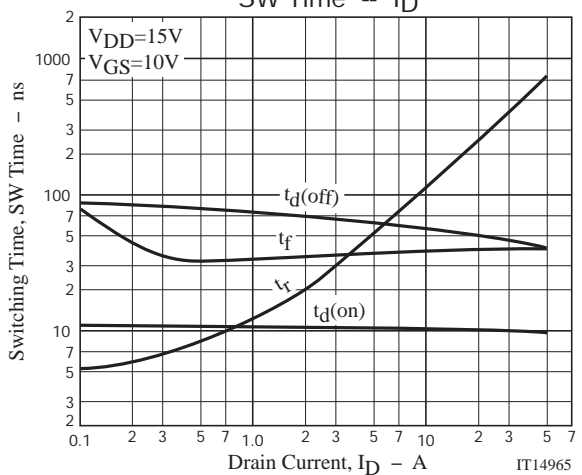
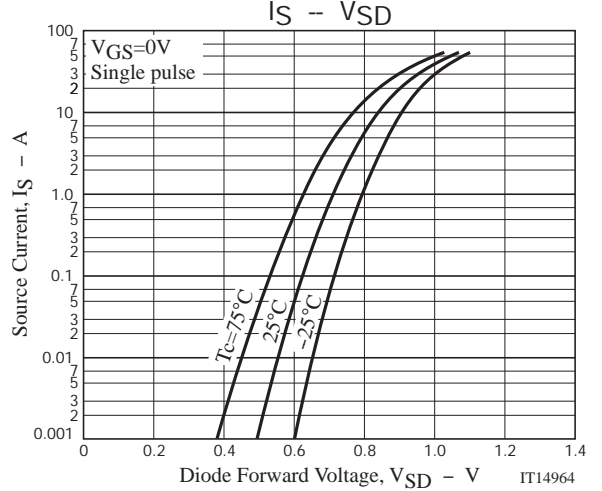
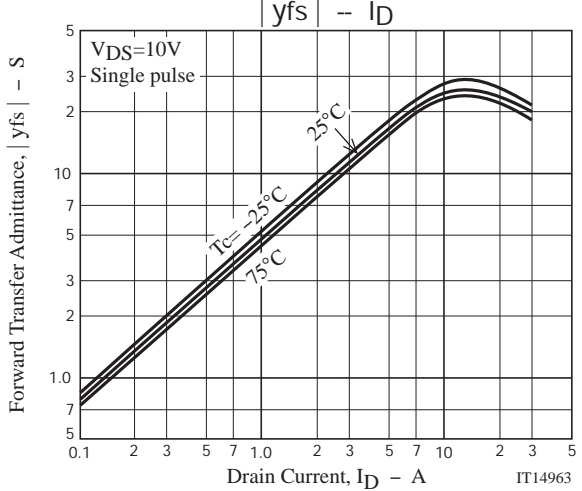
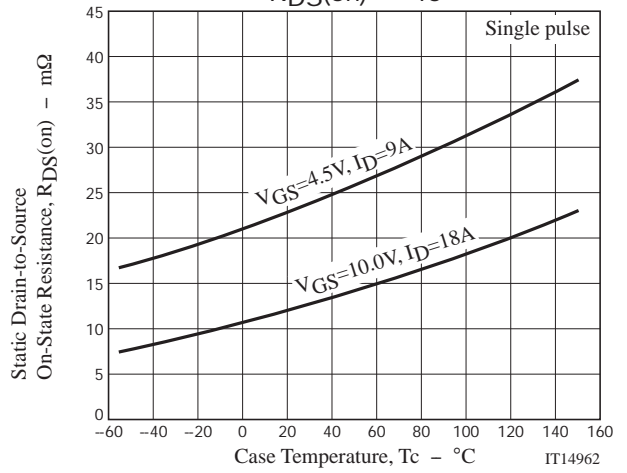
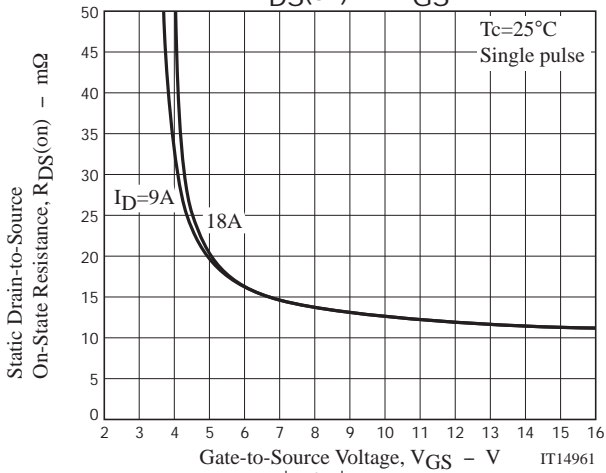
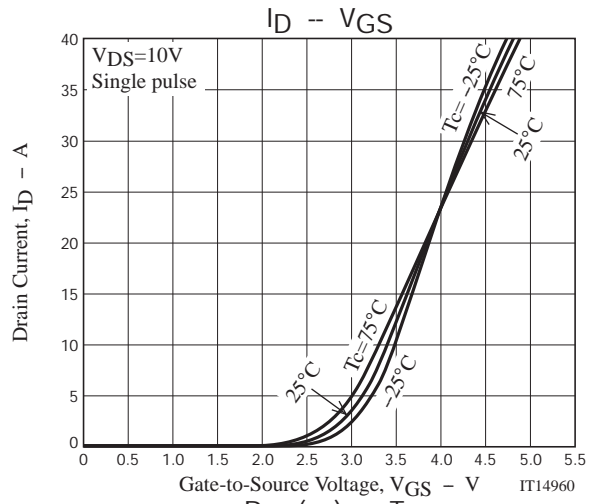
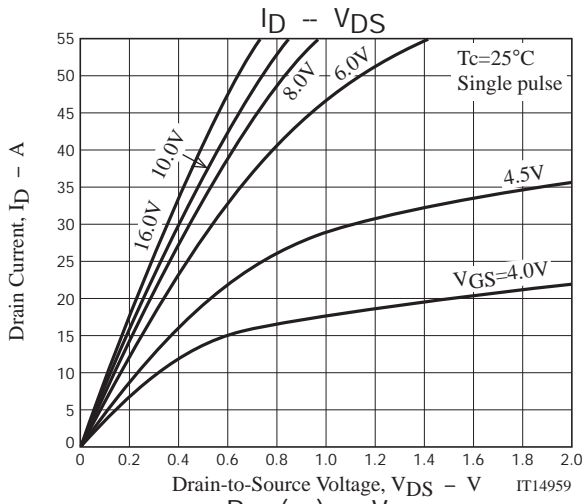
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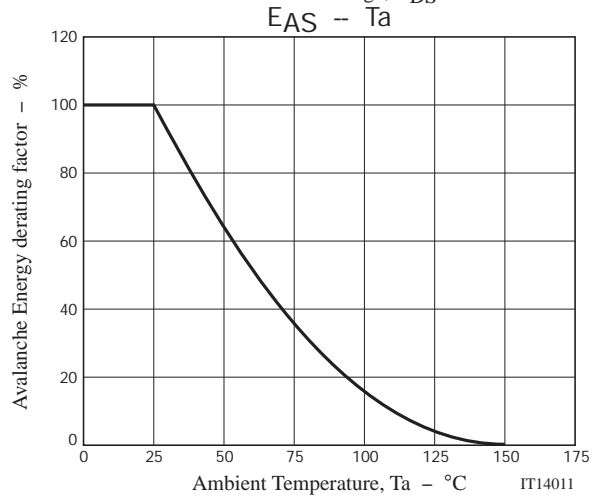
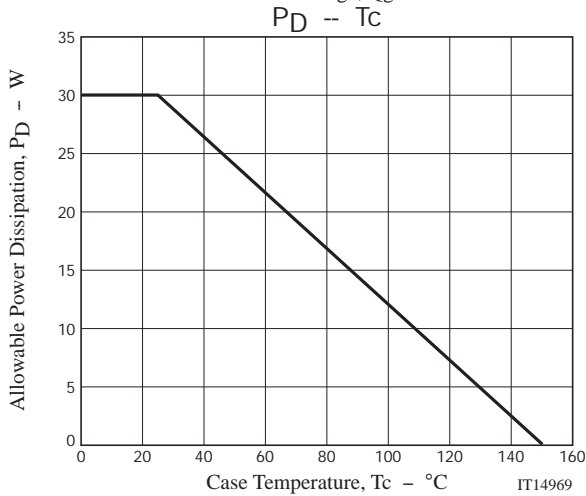
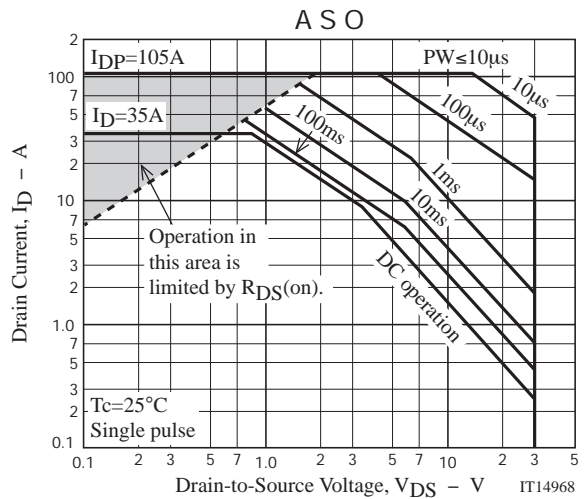
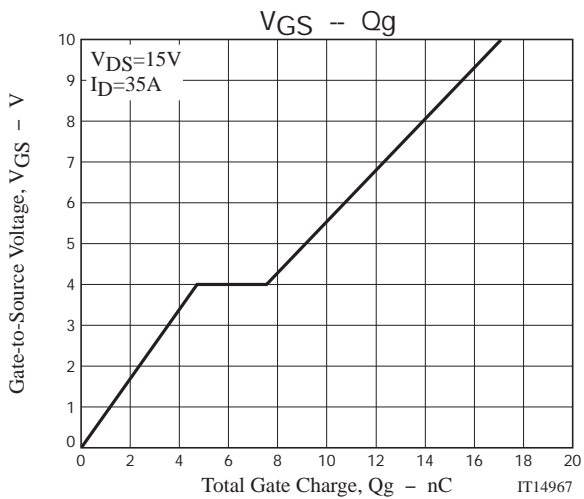
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## Switching Time Test Circuit







Note on usage : Since the ATP201 is a MOSFET product, please avoid using this device in the vicinity of highly charged objects.

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